

EM1Y-EM1C

Plastic Silicon Rectifiers

VOLTAGE RANGE: 100 --- 1000 V

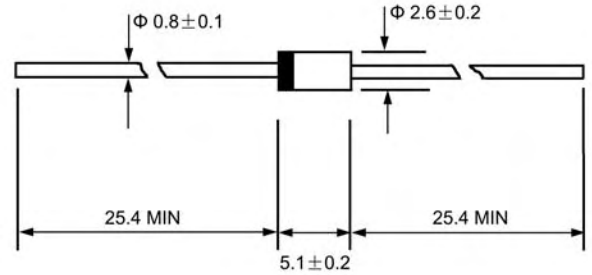
CURRENT: 1.0 A



DO - 41

Features

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned with Freon, Alcohol, Isopropanol and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0



Dimensions in millimeters

Mechanical Data

- ◇ Case: JEDEC DO--41, molded plastic
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.012 ounces, 0.34 grams
- ◇ Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		EM1Y	EM1Z	EM1	EM1A	EM1B	EM1C	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	100	200	400	600	800	1000	V
Maximum average forward rectified current 9.5mm lead length, @ $T_A=75^\circ C$	$I_{F(AV)}$	1.0						A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load @ $T_J=125^\circ C$	I_{FSM}	45.0						A
Maximum instantaneous forward voltage @ 1.0 A	V_F	0.97						V
Maximum reverse current @ $T_A=25^\circ C$ at rated DC blocking voltage @ $T_A=100^\circ C$	I_R	5.0 50.0						μA
Typical junction capacitance (Note1)	C_J	15						pF
Typical thermal resistance (Note2)	$R_{\theta JA}$	50						$^\circ C/W$
Operating junction temperature range	T_J	- 55---- +150						$^\circ C$
Storage temperature range	T_{STG}	- 55---- + 150						$^\circ C$

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Thermal resistance from junction to ambient.

Ratings AND Characteristic Curves

FIG.1 – FORWARD DERATING CURVE

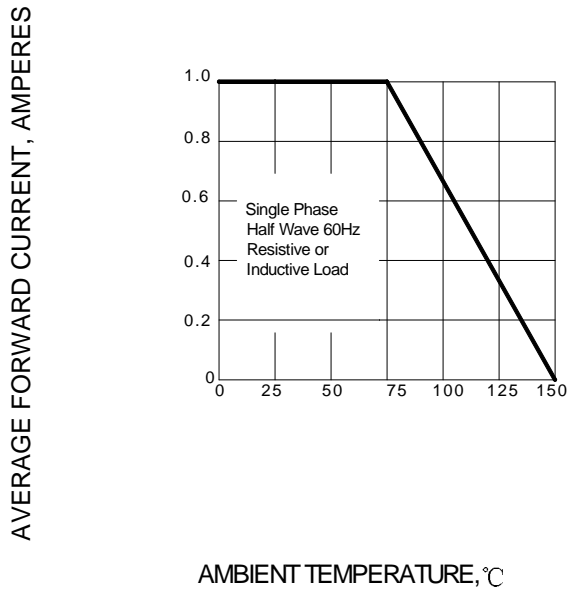


FIG.2 – TYPICAL FORWARD CHARACTERISTICS

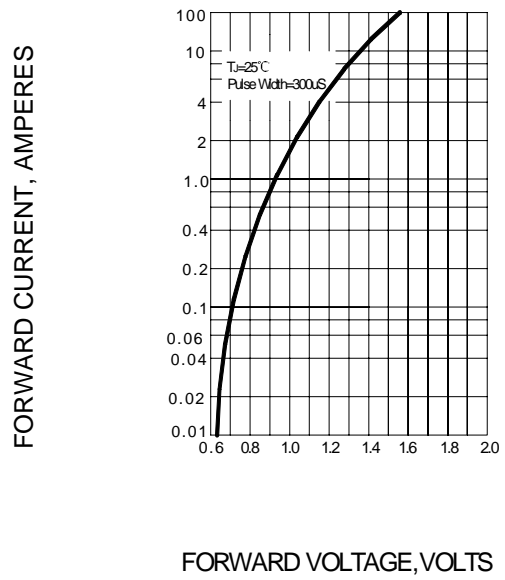


FIG.3 – PEAK FORWARD SURGE CURRENT

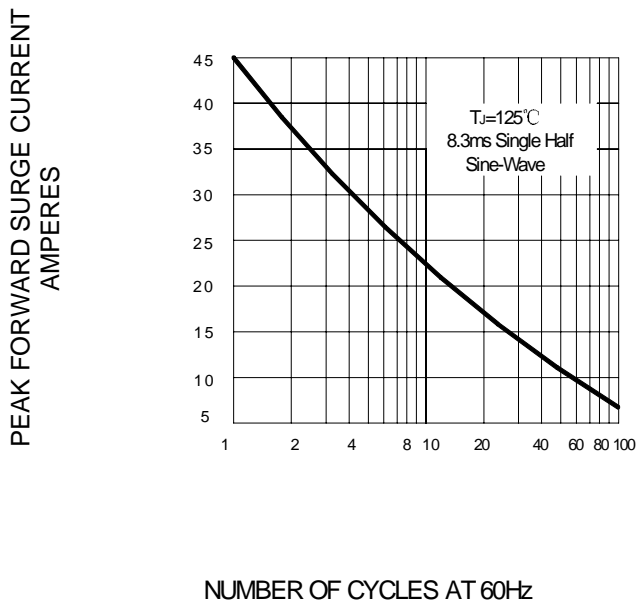


FIG.5 – TYPICAL JUNCTION CAPACITANCE

